

54F/74F533 Octal Transparent Latch with TRI-STATE® Outputs

General Description

The 'F533 consists of eight latches with TRI-STATE outputs for bus organized system applications. The flip-flops appear transparent to the data when Latch Enable (LE) is HIGH. When LE is LOW, the data that meets the setup times is latched. Data appears on the bus when the Output Enable $(\overline{\text{OE}})$ is LOW. When $\overline{\text{OE}}$ is HIGH the bus output is in the high impedance state. The 'F533 is the same as the 'F373, except that the outputs are inverted.

Features

- Eight latches in a single package
- TRI-STATE outputs for bus interfacing
- Inverted version of the 'F373
- Guaranteed 4000V minimum ESD protection

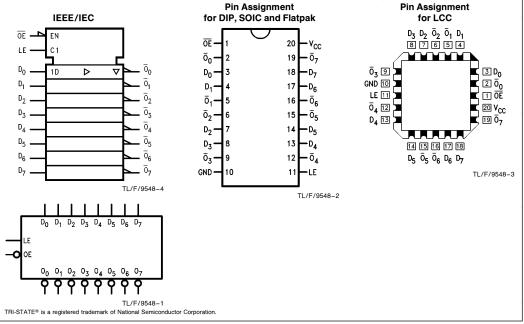
Commercial	Military	Package Number	Package Description		
74F533PC		N20A	20-Lead (0.300" Wide) Molded Dual-In-Line		
	54F533DM (Note 2)	J20A	20-Lead Ceramic Dual-In-Line		
74F533SC (Note 1)		M20B	20-Lead (0.300" Wide) Molded Small Outline, JEDEC		
74F533SJ (Note 1)		M20D	20-Lead (0.300" Wide) Molded Small Outline, EIAJ		
	54F533FM (Note 2)	W20A	20-Lead Cerpack		
	54F533LM (Note 2)	E20A	20-Lead Ceramic Leadless Chip Carrier, Type C		

Note 1: Devices also available in 13" reel. Use suffix = SCX and SJX.

Note 2: Military grade device with environmental and burn-in processing. Use suffix = DMQB, FMQB and LMQB.

Logic Symbols

Connection Diagrams



Unit Loading/Fan Out

		54F/74F			
Pin Names	Description	U.L. HIGH/LOW	Input I _{IH} /I _{IL} Output I _{OH} /I _{OL}		
D ₀ -D ₇	Data Inputs	1.0/1.0	20 μA/ -0.6 mA		
LE	Latch Enable Input (Active HIGH)	1.0/1.0	20 μA/ – 0.6 mA		
ŌĒ	Output Enable Input (Active LOW)	1.0/1.0	20 μA/ - 0.6 mA		
$\overline{O}_0 - \overline{O}_7$	Complementary TRI-STATE Outputs	150/40 (33.3)	−3 mA/24 mA (20 mA)		

Function Table

	Output		
LE	ō		
Н	L	Н	L
Н	L	L	Н
L	L	X	Ō₀ <i>z</i>
X	Н	Χ	Z

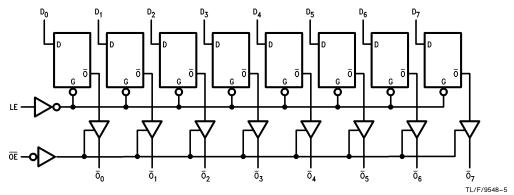
H = HIGH Voltage Level L = LOW Voltage Level

X = Immaterial

Functional Description

The 'F533 contains eight D-type latches with TRI-STATE output buffers. When the Latch Enable (LE) input is HIGH, data on the Dn inputs enters the latches. In this condition the latches are transparent, i.e., a latch output will change state each time its D input changes. When LE is LOW, the latches store the information that was present on the D inputs a setup time preceding the HIGH-to-LOW transition of LE. The TRI-STATE buffers are controlled by the Output Enable (OE) input. When OE is LOW, the buffers are in the bi-state mode. When $\overline{\text{OE}}$ is HIGH the buffers are in the high impedance mode but this does not interfere with entering new data into the latches.

Logic Diagram



Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

 $\begin{array}{lll} \text{Storage Temperature} & -65^{\circ}\text{C to} + 150^{\circ}\text{C} \\ \text{Ambient Temperature under Bias} & -55^{\circ}\text{C to} + 125^{\circ}\text{C} \\ \text{Junction Temperature under Bias} & -55^{\circ}\text{C to} + 175^{\circ}\text{C} \\ \text{Plastic} & -55^{\circ}\text{C to} + 150^{\circ}\text{C} \\ \end{array}$

V_{CC} Pin Potential to

Ground Pin -0.5V to +7.0V Input Voltage (Note 2) -0.5V to +7.0V Input Current (Note 2) -30 mA to +5.0 mA

Voltage Applied to Output in HIGH State (with $V_{CC} = 0V$)

 $\begin{array}{lll} \text{Standard Output} & -0.5 \text{V to V}_{\text{CC}} \\ \text{TRI-STATE Output} & -0.5 \text{V to } +5.5 \text{V} \end{array}$

Current Applied to Output in LOW State (Max)

in LOW State (Max) twice the rated I_{OL} (mA) ESD Last Passing Voltage (Min) 4000V

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

Recommended Operating Conditions

Free Air Ambient Temperature

Supply Voltage

Military + 4.5V to + 5.5V Commercial + 4.5V to + 5.5V

DC Electrical Characteristics

Symbol Parameter		54F/74F			Units	Vaa	Conditions	
Symbol	Parame	eter	Min Typ Max		Units	V _{CC}	Conditions	
V _{IH}	Input HIGH Voltage		2.0			V		Recognized as a HIGH Signal
V_{IL}	Input LOW Voltage				0.8	V		Recognized as a LOW Signal
V_{CD}	Input Clamp Diode Vo	oltage			-1.2	V	Min	$I_{\text{IN}} = -18 \text{mA}$
V _{OH}	Output HIGH 54F 10% V _{CC} Voltage 54F 10% V _{CC} 74F 10% V _{CC} 74F 10% V _{CC} 74F 5% V _{CC} 74F 5% V _{CC}		2.5 2.4 2.5 2.4 2.7 2.7			V	Min	$\begin{split} I_{OH} &= -1 \text{ mA} \\ I_{OH} &= -3 \text{ mA} \\ I_{OH} &= -1 \text{ mA} \\ I_{OH} &= -3 \text{ mA} \\ I_{OH} &= -1 \text{ mA} \\ I_{OH} &= -3 \text{ mA} \\ \end{split}$
V _{OL}	Output LOW 54F 10% V _{CC} Voltage 74F 10% V _{CC}				0.5 0.5	٧	Min	I _{OL} = 20 mA I _{OL} = 24 mA
I _{IH}	Input HIGH 54F Current 74F				20.0 5.0	μΑ	Max	V _{IN} = 2.7V
I _{BVI}	Input HIGH Current Breakdown Test	54F 74F			100 7.0	μΑ	Max	V _{IN} = 7.0V
I _{BVIT}	Input HIGH Current Breakdown (I/O)	54F 74F			1.0 0.5	mA	Max	V _{IN} = 5.5V
I _{CEX}	Output HIGH Leakage Current	54F 74F			250 50	μΑ	Max	$V_{OUT} = V_{CC}$
V_{ID}	Input Leakage Test	74F	4.75			٧	0.0	$I_{\text{ID}} = 1.9 \mu\text{A}$ All Other Pins Grounded
I _{OD}	Output Leakage Circuit Current	74F			3.75	μΑ	0.0	V _{IOD} = 150 mV All Other Pins Grounded
I _{IL}	Input LOW Current				-0.6	mA	Max	V _{IN} = 0.5V
lozh	Output Leakage Current				50	μΑ	Max	V _{OUT} = 2.7V
l _{OZL}	Output Leakage Current				-50	μΑ	Max	V _{OUT} = 0.5V
I _{OS}	Output Short-Circuit Current		-60		-150	mA	Max	V _{OUT} = 0V
I_{ZZ}	Bus Drainage Test				500	μΑ	0.0V	V _{OUT} = 5.25V
I _{CCZ}	Power Supply Curren	t		41	61	mA	Max	V _O = HIGH Z

AC Electrical Characteristics

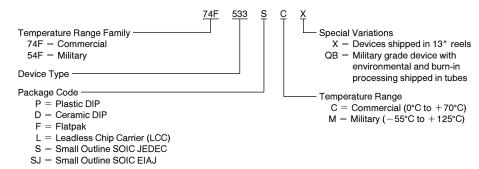
Symbol	Parameter				54F T _A , V _{CC} = Mil C _L = 50 pF		74F T _A , V _{CC} = Com C _L = 50 pF		Units
		Min	Тур	Max	Min	Max	Min	Max]
t _{PLH}	Propagation Delay D_n to \overline{O}_n	4.0 2.5	6.7 4.4	9.0 7.0	4.0 2.5	12.0 9.0	4.0 2.5	10.0 8.0	ns
t _{PLH}	Propagation Delay LE to On	5.0 3.0	7.1 4.7	11.0 7.0	5.0 3.0	14.0 9.0	5.0 3.0	13.0 8.0	ns
t _{PZH}	Output Enable Time	2.0 2.0	5.9 5.6	10.0 7.5	2.0 2.0	12.5 10.5	2.0 2.0	11.0 8.5	ns
t _{PHZ}	Output Disable Time	1.5 1.5	3.4 2.7	6.5 5.5	1.5 1.5	8.5 7.5	1.5 1.5	7.0 6.5	ns

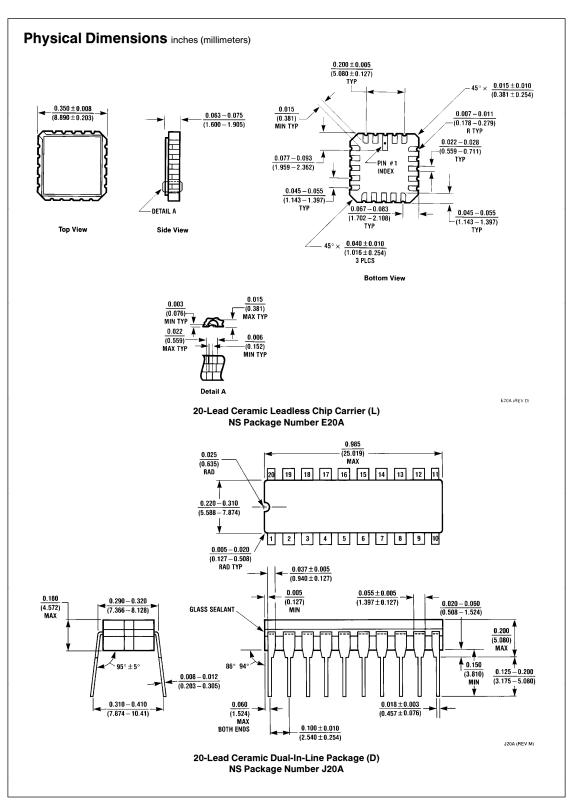
AC Operating Requirements

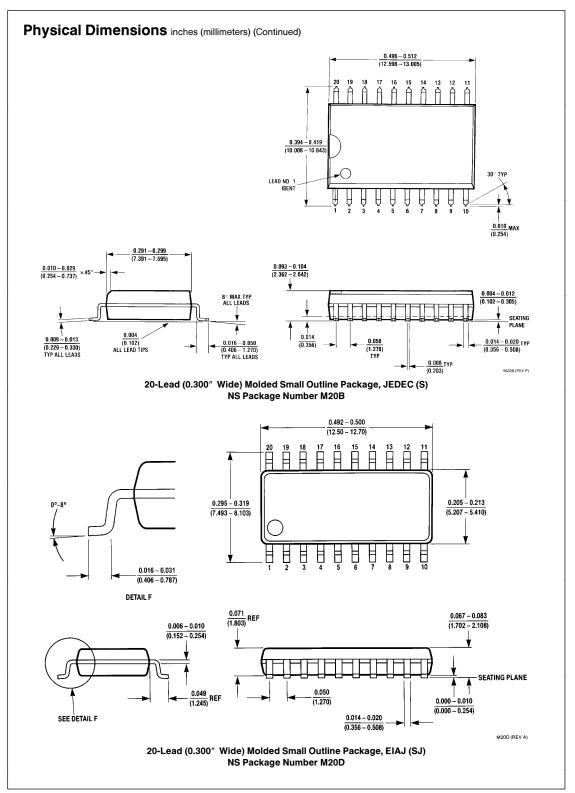
		$74F$ $T_A = +25^{\circ}C$ $V_{CC} = +5.0V$		54	F	74F		
Symbol	Parameter			$T_A, V_{CC} = Mil$		T _A , V _{CC} = Com		Units
		Min	Max	Min	Max	Min	Max]
t _S (H)	Setup Time, HIGH or LOW D _n to LE	2.0 2.0		2.0 2.0		2.0 2.0		ns
t _h (H)	Hold Time, HIGH or LOW D _n to LE	3.0 3.0		3.0 3.0		3.0 3.0		ns
t _w (H)	LE Pulse Width, HIGH	6.0		6.0		6.0		ns

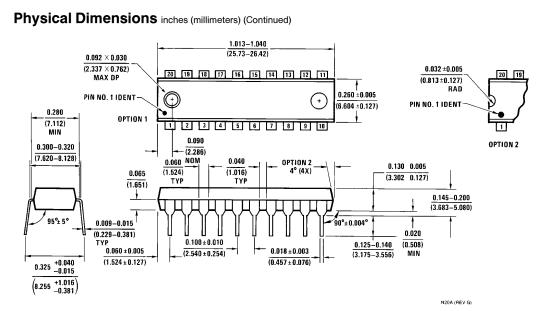
Ordering Information

The device number is used to form part of a simplified purchasing code where a package type and temperature range are defined as follows:



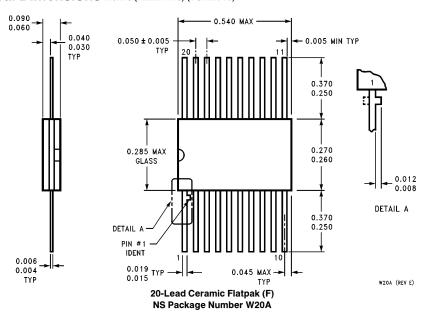






20-Lead (0.300" Wide) Molded Dual-In-Line Package (P) NS Package Number N20A

Physical Dimensions inches (millimeters) (Continued)



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- A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



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